
Graphene, Ge/III-V, Nanowires, and Emerging Materials for Post-CMOS Applications 4

Editors:

Y. Obeng

National Institute of Standards and Technology
Gaithersburg, Maryland, USA

S. De-Gendt

IMEC
Leuven, Belgium

Z. Karim

AIXTRON, Inc.
Sunnyvale, California, USA

D. Misra

New Jersey Institute of Technology
Newark, New Jersey, USA

P. Srinivasan

Texas Instruments
Dallas, Texas, USA

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Fax 609.737.2743
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